

Fast Recovery Diodes (Stud Version), 40 A/70 A/85 A



DO-203AB (DO-5)

FEATURES

- · Short reverse recovery time
- · Low stored charge
- · Wide current range
- Excellent surge capabilities
- Stud cathode and stud anode versions
- Types up to 100 V_{RRM}
- Compliant to RoHS directive 2002/95/EC

TYPICAL APPLICATIONS

- DC power supplies
- Inverters
- Converters
- Choppers
- · Ultrasonic systems
- · Freewheeling diodes

PRODUCT SUMMARY					
I _{F(AV)}	40 A/70 A/85 A				
-					

MAJOR RATINGS AND CHARACTERISTICS							
SYMBOL	CHARACTERISTICS	40HFL 70HFL 85HFL		UNITS			
1		40	70	85	A		
I _{F(AV)}	Maximum T _C	85	85	85	°C		
I	50 Hz	400	700	1100	Δ.		
I _{FSM}	60 Hz	420	730	1151	А		
l ² t	50 Hz	800	2450	6050	A ² s		
-	60 Hz	730	2240	5523	A-S		
I²√t		11 300 34 650 85 560		l²√s			
V _{RRM}	Range	100 to 1000 V					
t _{rr}		See Recovery Characteristics table ns					
TJ	Range	- 40 to 125 °C					

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40HFL, 70HFL, 85HFL Series

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ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS						
TYPE NUMBER (1)	V _{RRM} , MAXIMUM PEAK REPETITIVE REVERSE VOLTAGE	V _{RSM} , MAXIMUM PEAK NON-REPETITIVE REVERSE VOLTAGE	I _{FM} , MAXIMUM PEAK REVERSE CURRENT AT RATED V _{RRM} mA			
	T _J = - 40 °C TO 125 °C V	T _J = 25 °C TO 125 °C V	T _J = 25 °C	T _J = 125 °C		
40HFL10S02, 40HFL10S05, 40HFL10S10	100	150				
40HFL20S02, 40HFL20S05, 40HFL20S10	200	300				
40HFL40S02, 40HFL40S05, 40HFL40S10	400	500	0.1	10		
40HFL60S02, 40HFL60S05, 40HFL60S10	600	700	0.1	10		
40HFL80S05, 40HFL80S10	800	900				
40HFL100S05, 40HFL100S10	1000	1100				
70HFL10S02, 70HFL10S05, 70HFL10S10	100	150				
70HFL20S02, 70HFL20S05, 70HFL20S10	200	300				
70HFL40S02, 70HFL40S05, 70HFL40S10	400	500	0.1	15		
70HFL60S02, 70HFL60S05, 70HFL60S10	600	700	0.1	15		
70HFL80S05, 70HFL80S10	800	900				
70HFL100S05, 70HFL100S10	1000	1100				
85HFL10S02, 85HFL10S05, 85HFL10S10	100	150				
85HFL20S02, 85HFL20S05, 85HFL20S10	200	300				
85HFL40S02, 85HFL40S05, 85HFL40S10	400	500	0.1	20		
85HFL60S02, 85HFL60S05, 85HFL60S10	600	700	0.1	20		
85HFL80S05, 85HFL80S10	800	900				
85HFL100S05, 85HFL100S10	1000	1100				

Note

⁽¹⁾ Types listed are cathode case, for anode case add "R" to code, i.e. 40HFLR20S02, 85HFLR100S05 etc.



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FORWARD CONDUCTION								
PARAMETER	SYMBOL	TE	40HFL	70HFL	85HFL	UNITS		
Maximum average forward current at maximum case temperature	I _{F(AV)}	180° conduc	40	70	85	A		
·	_				75	1	°C	
Maximum RMS forward current	I _{F(RMS)}			63	110	134	Α	
Maximum peak repetitive forward current	I _{FRM}	Sinusoidal h	alf wave, 30° conduction	220	380	470	Α	
		t = 10 ms	Sinusoidal half wave, 100 % V _{BBM} reapplied,	400	700	1100	- A	
Maximum peak, one-cycle non-repetitive forward current	I _{FSM}	t = 8.3 ms	initial T _J = T _J maximum Sinusoidal half wave, no voltage reapplied,	420	730	1151		
		t = 10 ms		475	830	1308		
		t = 8.3 ms	initial $T_J = T_J$ maximum	500	870	1369		
	l ² t	t = 10 ms	100 % V _{RRM} reapplied,	800	2450	6050		
Maximum 12t for fraing		t = 8.3 ms	initial $T_J = T_J$ maximum	730	2240	5523		
Maximum I ² t for fusing	1-1		No voltage reapplied,	1130	3460	8556	A-S	
		$t = 8.3 \text{ ms}$ initial $T_J = T_J \text{ maximum}$		$t = 8.3 \text{ ms}$ initial $T_J = T_J \text{ maximum}$	1030	3160	7810	
Maximum $I^2\sqrt{t}$ for fusing ⁽¹⁾	I²√t	t = 0.1 ms to 10 ms, no voltage reapplied		11 300	34 650	85 560	A²√s	
Maximum value of threshold voltage	V _{F(TO)}	- T _J = 125 °C		1.081	1.085	1.128	V	
Maximum value of forward slope resistance	r _F			6.33	3.40	2.11	mΩ	
Maximum forward voltage drop	V_{FM}	T _J = 25 °C, I	1.95	1.85	1.75	V		

Note

⁽¹⁾ I^2t for time $t_x = I^2\sqrt{t} \cdot \sqrt{t_x}$

RECOVERY CHARACTERISTICS												
PARAMETER SYMBOL	TEST CONDITIONS	40HFL			70HFL			85HFL			UNITS	
PARAMETER	STIVIBUL	TEST CONDITIONS	S02	S05	S10	S02	S05	S10	S02	S05	S10	UNITS
Typical reverse	+	$T_J = 25 ^{\circ}\text{C}$, $I_F = 1 \text{A to V}_R = 30 \text{V}$, $- \text{d}I_F / \text{d}t = 100 \text{A}/\mu\text{s}$	70	180	350	60	150	290	50	120	270	ns
recovery time	overy time t _{rr}	$T_J = 25$ °C, - $dI_F/dt = 25$ A/ μ s, $I_{FM} = \pi x \text{ rated } I_{F(AV)}$	200	500	1000	200	500	1000	200	500	1000	115
Typical reverse	$T_J = 25 ^{\circ}\text{C}$, $I_F = 1 \text{A to V}_R = 30 \text{V}$, - $dI_F/dt = 100 \text{A/}\mu\text{s}$	160	750	3100	90	500	1600	70	340	1350	nC	
recovered charge	Q _{rr}	Q_{rr} $T_J = 25 \text{ °C, - dI}_F/\text{dt} = 25 \text{ A/}\mu\text{s,}$ $I_{FM} = \pi \text{ x rated } I_{F(AV)}$		1300	6000	240	1300	6000	240	1300	6000	110

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THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	40HFL	70HFL	85HFL	UNITS
Junction operating temperature range	T_J		- 40 to 125		°C	
Storage temperature range	T _{Stg}			- 40 to 150)	
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	0.60	0.36	0.30	K/W
Maximum thermal resistance, case to heatsink	R _{thCS}	Mounting surface, smooth, flat and greased 0.25			I N/VV	
		Not lubricated thread, tighting on nut (1)		3.4 (30)		
Maximum allowable mounting torque (+ 0 %, - 10 %)		Lubricated thread, tighting on nut (1)	2.3 (20)			N · m
		Not lubricated thread, tighting on hexagon (2)		4.2 (37)		
		Lubricated thread, tighting on hexagon (2)	3.2 (28)			
Approximate weight				25		
Approximate weight				0.88		
Case style		JEDEC		DO-203A	B (DO-5)	•

Notes

- (1) Recommended for pass-through holes
- (2) Recommended for holed threaded heatsinks

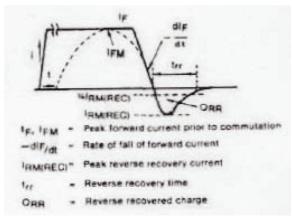


Fig. 1 - Reverse Recovery Time Test Waveform

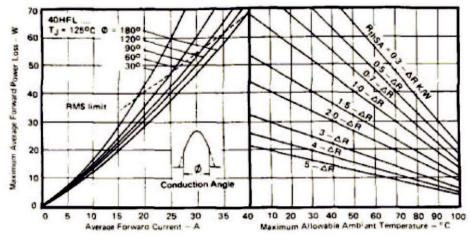
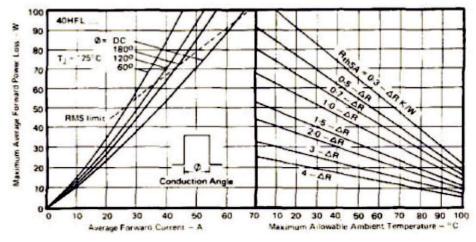




Fig. 2 - Current Rating Nomogram (Sinusoidal Waveforms), 40HFL Series



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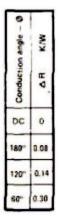
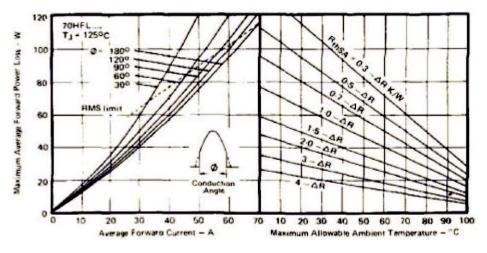


Fig. 3 - Current Rating Nomogram (Rectangular Waveforms), 40HFL Series



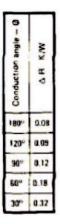
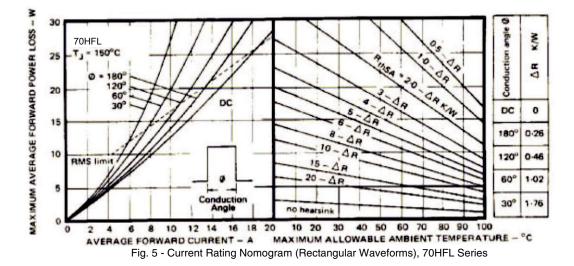


Fig. 4 - Current Rating Nomogram (Sinusoidal Waveforms), 70HFL Series



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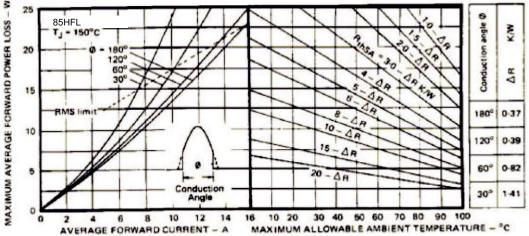


Fig. 6 - Current Rating Nomogram (Sinusoidal Waveforms), 85HFL Series

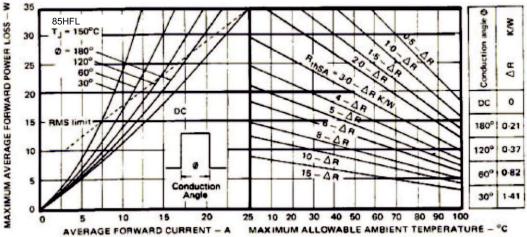


Fig. 7 - Current Rating Nomogram (Rectangular Waveforms), 85HFL Series

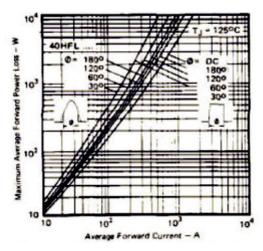


Fig. 8 - Maximum High Level Forward Power Loss vs. Average Forward Current, 40HFL Series

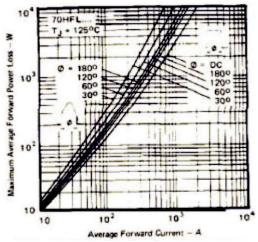


Fig. 9 - Maximum High Level Forward Power Loss vs. Average Forward Current, 70HFL Series



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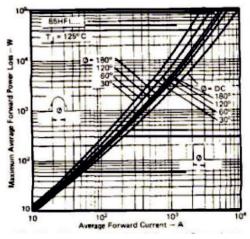


Fig. 10 - Maximum High Level Forward Power Loss vs. Average Forward Current, 85HFL Series

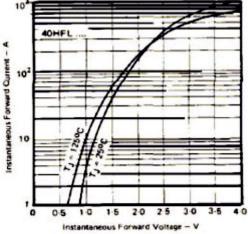


Fig. 11 - Maximum Forward Voltage vs. Forward Current, 40HFL Series

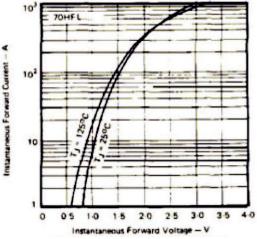


Fig. 12 - Maximum Forward Voltage vs. Forward Current, 70HFL Series

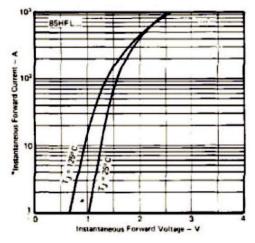


Fig. 13 - Maximum Forward Voltage vs. Forward Current, 85HFL Series

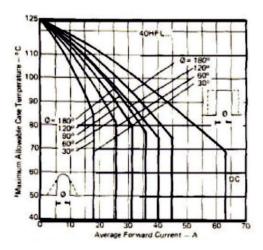


Fig. 14 - Average Forward Current vs. Maximum Allowable Case Temperature, 40HFL Series

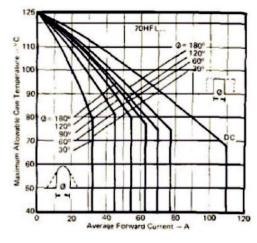


Fig. 15 - Average Forward Current vs. Maximum Allowable Case Temperature, 70HFL Series

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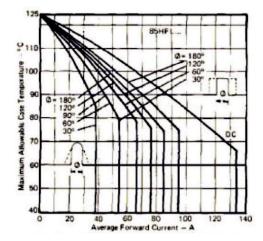


Fig. 16 - Average Forward Current vs. Maximum Allowable Case Temperature, 85HFL Series

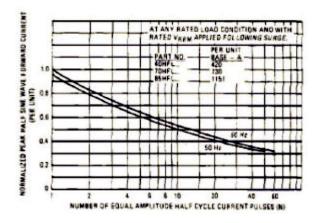


Fig. 17 - Maximum Non-Repetitive Surge Current vs. Number of Current Pulses, All Series

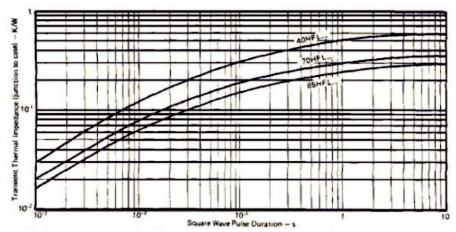


Fig. 18 - Maximum Transient Thermal Impedance, Junction to Case vs. Pulse Duration, All Series

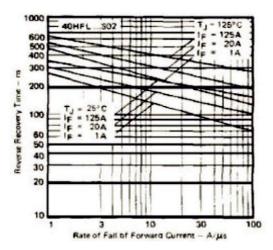


Fig. 19 - Typical Reverse Recovery Time vs. Rate of Fall of Forward Current, 40HFL...S02 Series

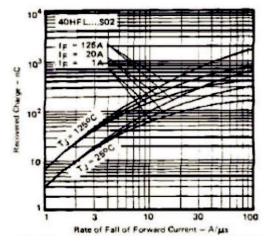


Fig. 20 - Typical Recovered Charge vs. Rate of Fall of Forward Current, 40HFL...S02 Series



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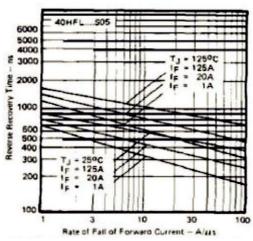


Fig. 21 - Typical Reverse Recovery Time vs. Rate of Fall of Forward Current, 40HFL...S05 Series

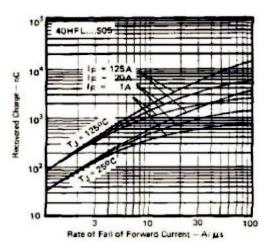


Fig. 22 - Typical Recovered Charge vs.
Rate of Fall of Forward Current, 40HFL...S05 Series

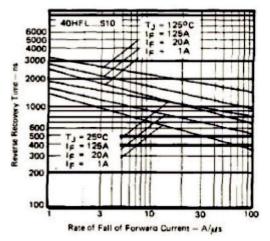


Fig. 23 - Typical Reverse Recovery Time vs. Rate of Fall of Forward Current, 40HFL...S10 Series

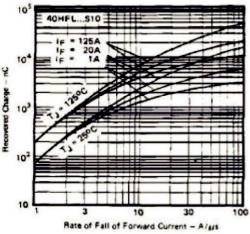


Fig. 24 - Typical Recovered Charge vs.
Rate of Fall of Forward Current, 40HFL...S10 Series

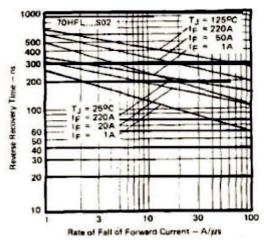


Fig. 25 - Typical Reverse Recovery Time vs. Rate of Fall of Forward Current, 70HFL...S02 Series

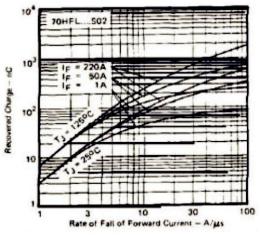


Fig. 26 - Typical Recovered Charge vs. Rate of Fall of Forward Current, 70HFL...S02 Series

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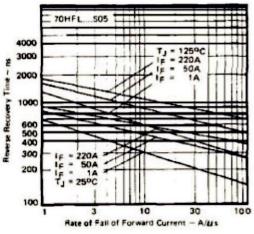


Fig. 27 - Typical Reverse Recovery Time vs. Rate of Fall of Forward Current, 70HFL...S05 Series

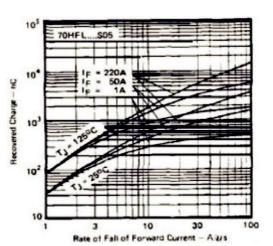


Fig. 28 - Typical Recovered Charge vs. Rate of Fall of Forward Current, 70HFL...S05 Series

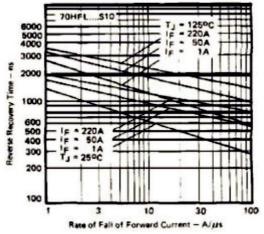


Fig. 29 - Typical Reverse Recovery Time vs. Rate of Fall of Forward Current, 70HFL...S10 Series

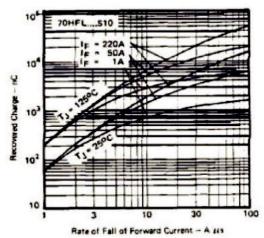


Fig. 30 - Typical Recovered Charge vs. Rate of Fall of Forward Current, 70HFL...S10 Series

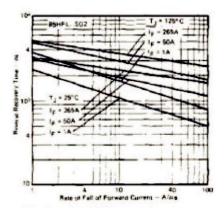


Fig. 31 - Typical Reverse Recovery Time vs. Rate of Fall of Forward Current, 85HFL...S02 Series

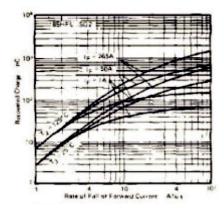
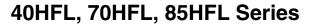


Fig. 32 - Typical Recovered Charge vs. Rate of Fall of Forward Current, 85HFL...S02 Series





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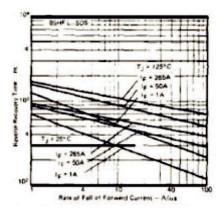


Fig. 33 - Typical Reverse Recovery Time vs. Rate of Fall of Forward Current, 85HFL...S05 Series

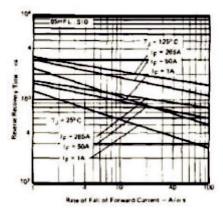


Fig. 35 - Typical Reverse Recovery Time vs. Rate of Fall of Forward Current, 85HFL...S10 Series

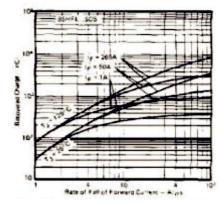


Fig. 34 - Typical Recovered Charge vs. Rate of Fall of Forward Current, 85HFL...S05 Series

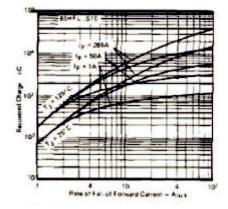


Fig. 36 - Typical Recovered Charge vs. Rate of Fall of Forward Current, 85HFL...S10 Series

LINKS TO RELAT	TED DOCUMENTS
Dimensions	www.vishay.com/doc?95312



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